

TSM1NB60SCT B0G

TSM1NB60SCT B0G Information

Heisener.com

Part Number TSM1NB60SCT B0G Manufacturer TSC America Inc.

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET, SINGLE, N-CHANNEL, PLANA

Package TO-226-3, TO-92-3 (TO-226AA)

For the pricing/inventory/lead time, please contact

us

For Reference Only

Website: https://www.heisener.com
E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

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TSM1NB60SCT B0G Specifications

| Manufacturer Part Number TSMINB60SCT B0G Manufacturer TSC America Inc. Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-226-3, TO-92-3 (TO-226AA) Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 500mA (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 6.1nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 138pF @ 25V Vgs (Max) ±39 V FET Feature - Power Dissipation (Max) 2.5W (Tc) Rds On (Max) @ Id, Vgs 10 Ohm @ 250mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92 Package / Case TO-226-3, TO-92-3 (TO-226AA) | | |
|--|--|--------------------------------------|
| Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-226-3, TO-92-3 (TO-226AA) Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 500mA (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 6.1nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 138pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 2.5W (Tc) Rds On (Max) @ Id, Vgs 10 Ohm @ 250mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92 Package / Case TO-226-3, TO-92-3 (TO-226AA) | Manufacturer Part Number | TSM1NB60SCT B0G |
| Package TO-226-3, TO-92-3 (TO-226AA) Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 500mA (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 6.1nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 138pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 2.5W (Tc) Rds On (Max) @ Id, Vgs 10 Ohm @ 250mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92 Package / Case TO-226-3, TO-92-3 (TO-226AA) | Manufacturer | TSC America Inc. |
| Package TO-226-3, TO-92-3 (TO-226AA) Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 500mA (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 6.1nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 138pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 2.5W (Tc) Rds On (Max) @ Id, Vgs 10 Ohm @ 250mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92 Package / Case TO-226-3, TO-92-3 (TO-226AA) | Category | Discrete Semiconductor Products |
| Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 500mA (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 6.1nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 138pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 2.5W (Tc) Rds On (Max) @ Id, Vgs 10 Ohm @ 250mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92 Package / Case TO-226-3, TO-92-3 (TO-226AA) | | Transistors - FETs, MOSFETs - Single |
| FET Type N-Channel Technology MOSFET (Metal Oxide) 600V Current - Continuous Drain (Id) @ 25°C 500mA (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 Ohm @ 250mA, 10V Perating Temperature Mounting Type Supplier Device Package Package / Case N-Channel MOSFET (Metal Oxide) MOSFET (Metal Oxide) MOSFET (Metal Oxide) 600V 600 | Package | TO-226-3, TO-92-3 (TO-226AA) |
| TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C500mA (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 250μAGate Charge (Qg) (Max) @ Vgs6.1nC @ 10VInput Capacitance (Ciss) (Max) @ Vds138pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)2.5W (Tc)Rds On (Max) @ Id, Vgs10 Ohm @ 250mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92Package / CaseTO-226-3, TO-92-3 (TO-226AA) | Series | - |
| Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C500mA (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 250μAGate Charge (Qg) (Max) @ Vgs6.1nC @ 10VInput Capacitance (Ciss) (Max) @ Vds138pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)2.5W (Tc)Rds On (Max) @ Id, Vgs10 Ohm @ 250mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92Package / CaseTO-226-3, TO-92-3 (TO-226AA) | FET Type | N-Channel |
| Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 6.1nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 138pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 Ohm @ 250mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92 Package / Case TO-226-3, TO-92-3 (TO-226AA) | Technology | MOSFET (Metal Oxide) |
| Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 6.1nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 138pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 2.5W (Tc) Rds On (Max) @ Id, Vgs 10 Ohm @ 250mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92 Package / Case TO-226-3, TO-92-3 (TO-226AA) | Drain to Source Voltage (Vdss) | 600V |
| Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 138pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 Ohm @ 250mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92 Package / Case TO-226-3, TO-92-3 (TO-226AA) | Current - Continuous Drain (Id) @ 25°C | 500mA (Tc) |
| Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 138pF @ 25V Vgs (Max) ±30V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 Ohm @ 250mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92 Package / Case 6.1nC @ 10V 6.1nC @ 10V 6.1nC @ 10V 138pF @ 25V 2.5W To- 10 Ohm 250mA, 10V 10 Ohm 250mA, 10V 10 Ohm 10 | Drive Voltage (Max Rds On, Min Rds On) | 10V |
| Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 Ohm @ 250mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92 Package / Case TO-226-3, TO-92-3 (TO-226AA) | Vgs(th) (Max) @ Id | 4.5V @ 250μA |
| Vgs (Max)±30VFET Feature-Power Dissipation (Max)2.5W (Tc)Rds On (Max) @ Id, Vgs10 Ohm @ 250mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92Package / CaseTO-226-3, TO-92-3 (TO-226AA) | Gate Charge (Qg) (Max) @ Vgs | 6.1nC @ 10V |
| FET Feature - Power Dissipation (Max) 2.5W (Tc) Rds On (Max) @ Id, Vgs 10 Ohm @ 250mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92 Package / Case TO-226-3, TO-92-3 (TO-226AA) | Input Capacitance (Ciss) (Max) @ Vds | 138pF @ 25V |
| Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 Ohm @ 250mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92 Package / Case TO-226-3, TO-92-3 (TO-226AA) | Vgs (Max) | ±30V |
| Rds On (Max) @ Id, Vgs 10 Ohm @ 250mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92 Package / Case TO-226-3, TO-92-3 (TO-226AA) | FET Feature | - |
| Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92 Package / Case TO-226-3, TO-92-3 (TO-226AA) | Power Dissipation (Max) | 2.5W (Tc) |
| Mounting Type Through Hole Supplier Device Package TO-92 Package / Case TO-226-3, TO-92-3 (TO-226AA) | Rds On (Max) @ Id, Vgs | 10 Ohm @ 250mA, 10V |
| Supplier Device Package TO-92 Package / Case TO-226-3, TO-92-3 (TO-226AA) | Operating Temperature | -55°C ~ 150°C (TJ) |
| Package / Case TO-226-3, TO-92-3 (TO-226AA) | Mounting Type | Through Hole |
| | Supplier Device Package | TO-92 |
| Report errors? | Package / Case | TO-226-3, TO-92-3 (TO-226AA) |
| | | Report errors? |

TSM1NB60SCT B0G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

TSM1NB60SCT B0G Payment Methods



















TSM1NB60SCT B0G Shipping Methods













If you have any question about TSM1NB60SCT B0G, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com